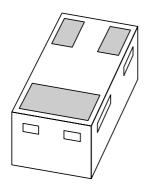
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BC857M series PNP general purpose transistors

Product specification Supersedes data of 2003 Jul 15 2004 Mar 10





# PNP general purpose transistors

## **BC857M series**

#### **FEATURES**

- Leadless ultra small plastic package (1 mm × 0.6 mm × 0.5 mm)
- Board space 1.3 × 0.9 mm
- Power dissipation comparable to SOT23.

#### **APPLICATIONS**

- General purpose small signal DC
- · Low and medium frequency AC applications
- Mobile communications, digital (still) cameras, PDAs, PCMCIA cards.

#### **DESCRIPTION**

PNP general purpose transistor in a SOT883 leadless ultra small plastic package.

NPN complement: BC847M series.

#### **MARKING**

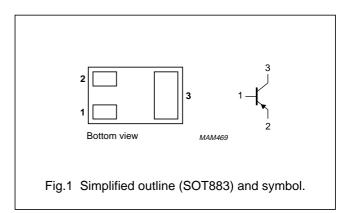
TYPE NUMBER	MARKING CODE
BC857AM	D1
BC857BM	D2
BC857CM	D3

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-45	<b>V</b>
I <sub>C</sub>	collector current (DC)	-100	mA
I <sub>CM</sub>	peak collector current	-200	mA

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
TIPE NOWBER	NAME DESCRIPTION		VERSION
BC857AM	<ul> <li>Leadless ultra small plastic package; 3 solder lands; body</li> </ul>		SOT883
BC857BM		1.0 x 0.6 x 0.5 mm	
BC857CM			

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	<b>-45</b>	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	<b>-</b> 5	٧
I <sub>C</sub>	collector current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-200	mA
I <sub>BM</sub>	peak base current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
		note 1	_	250	mW
		note 2	_	430	mW
T <sub>stg</sub>	storage temperature		<b>–</b> 65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### **Notes**

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60  $\mu$ m copper strip line.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm<sup>2</sup>.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		
		note 1	500	K/W
		note 2	290	K/W

#### Notes

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm<sup>2</sup>.

# PNP general purpose transistors

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#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V; } I_E = 0$	_	-15	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	-5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$			
	BC857AM		125	250	
	BC857BM		220	475	
	BC857CM		420	800	
V <sub>BE</sub>	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	_	-820	mV
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-200	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note } 1$	_	-400	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	2.5	pF
f⊤	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ f = 100 MHz	100	_	MHz
F	noise figure	$I_C = -200 \mu A; V_{CE} = -5 V;$ $R_S = 2 k\Omega; f = 1 kHz; B = 200 Hz$	_	10	dB

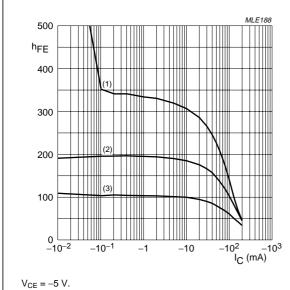
#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

# PNP general purpose transistors

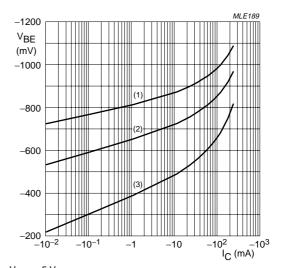
#### BC857M series

#### **GRAPHICAL INFORMATION BC857AM**



- (1) T<sub>amb</sub> = 150 °C.
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

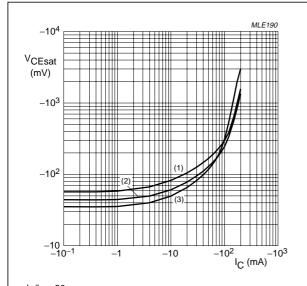
Fig.2 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

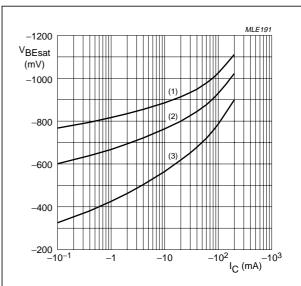
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

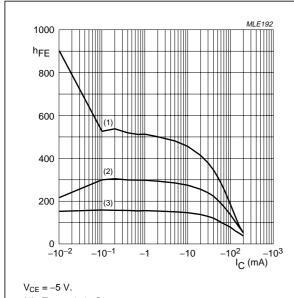
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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# PNP general purpose transistors

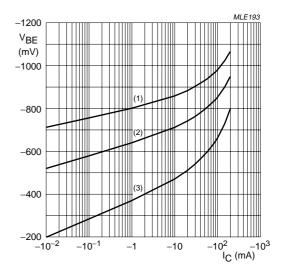
#### BC857M series

#### **GRAPHICAL INFORMATION BC857BM**



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

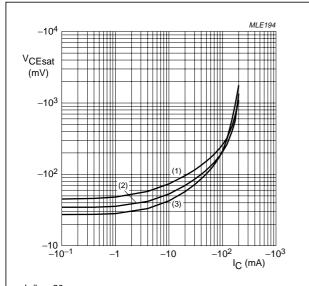
Fig.6 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

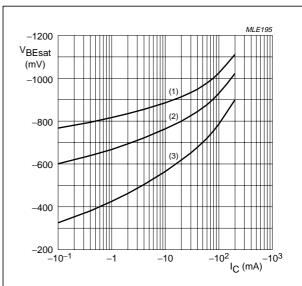
Fig.7 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B}=20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

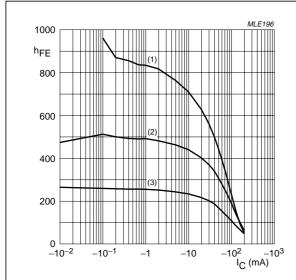
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

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#### BC857M series

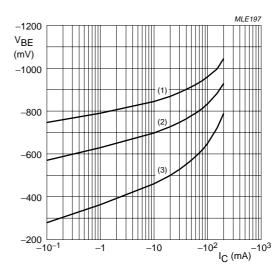
#### **GRAPHICAL INFORMATION BC857CM**



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

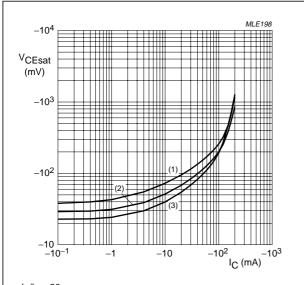
Fig.10 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

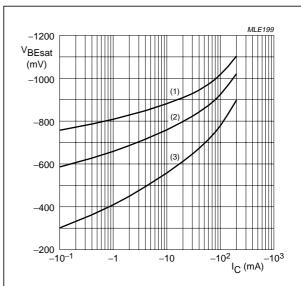
Fig.11 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

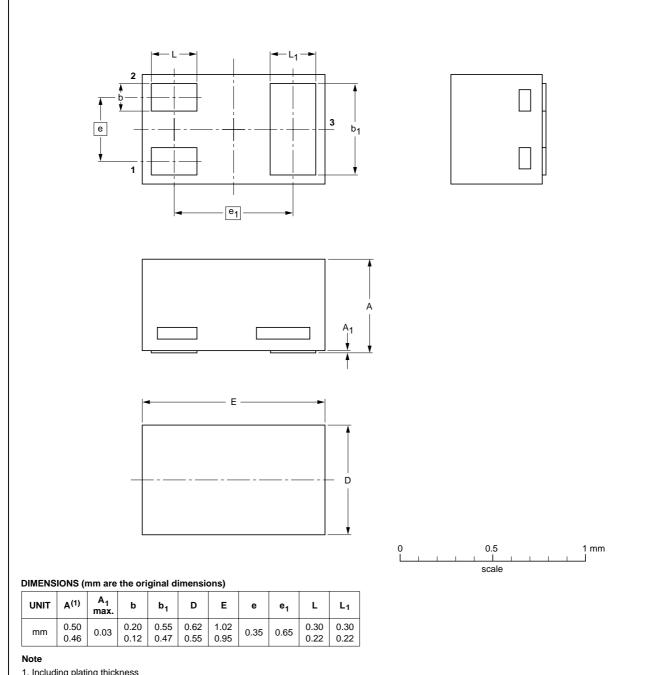
# PNP general purpose transistors

## BC857M series

#### **PACKAGE OUTLINE**

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

**SOT883** 



1. Including plating thickness

OUTLINE	INE REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT883			SC-101			<del>03-02-05</del> 03-04-03

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# PNP general purpose transistors

#### BC857M series

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Printed in The Netherlands

R75/02/pp10

Date of release: 2004 Mar 10

Document order number: 9397 750 12839

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